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Semiconductor devices - Mechanical and climatic test methods - Part 28: Electrostatic discharge (ESD) sensitivity testing - Charged device model (CDM) - device level

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April 2022

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Supersedes EN 60749-28:2017 and all of its
amendments and corrigenda (if any)

English Version

**Semiconductor devices - Mechanical and climatic test methods -
Part 28: Electrostatic discharge (ESD) sensitivity testing -
Charged device model (CDM) - device level
(IEC 60749-28:2022)**

Dispositifs à semiconducteurs - Méthodes d'essai
mécaniques et climatiques - Partie 28: Essai de sensibilité
aux décharges électrostatiques (DES) - Modèle de dispositif
chargé (CDM) - niveau du dispositif
(IEC 60749-28:2022)

Halbleiterbauelemente - Mechanische und klimatische
Prüfverfahren - Teil 28: Prüfung der Empfindlichkeit gegen
elektrostatische Entladungen (ESD) - Charged Device
Model (CDM) - Device Level
(IEC 60749-28:2022)

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Europäisches Komitee für Elektrotechnische Normung

CEN-CENELEC Management Centre: Rue de la Science 23, B-1040 Brussels

EN IEC 60749-28:2022 (E)**European foreword**

The text of document 47/2746/FDIS, future edition 2 of IEC 60749-28, prepared by IEC/TC 47 "Semiconductor devices" was submitted to the IEC-CENELEC parallel vote and approved by CENELEC as EN IEC 60749-28:2022.

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In the official version, for Bibliography, the following note has to be added for the standard indicated:

IEC 60749-26 NOTE Harmonized as EN IEC 60749-26



IEC 60749-28

Edition 2.0 2022-03

INTERNATIONAL STANDARD

NORME INTERNATIONALE



**Semiconductor devices – Mechanical and climatic test methods –
Part 28: Electrostatic discharge (ESD) sensitivity testing – Charged device model
(CDM) – device level**

**Dispositifs à semiconducteurs – Méthodes d’essais mécaniques et
climatiques –**

**Partie 28: Essai de sensibilité aux décharges électrostatiques (DES) – Modèle de
dispositif chargé (CDM) – niveau du dispositif**

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IEC Secretariat
3, rue de Varembe
CH-1211 Geneva 20
Switzerland

Tel.: +41 22 919 02 11
info@iec.ch
www.iec.ch

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INTERNATIONAL STANDARD

NORME INTERNATIONALE



**Semiconductor devices – Mechanical and climatic test methods –
Part 28: Electrostatic discharge (ESD) sensitivity testing – Charged device
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INTERNATIONAL ELECTROTECHNICAL COMMISSION

**SEMICONDUCTOR DEVICES –
MECHANICAL AND CLIMATIC TEST METHODS –****Part 28: Electrostatic discharge (ESD) sensitivity testing –
Charged device model (CDM) – device level**

FOREWORD

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ANSI/ESDA/JEDEC JS-002-2018 has served as a basis for the elaboration of this standard. It is used with permission of the copyright holders, ESD Association and JEDEC Solid state Technology Association. ANSI/ESDA/JEDEC JS-002-2018 describes the field-induced (FI) method. An alternative, the direct contact (DC) method (not based on JS-002-2018), is described in Annex J.

This second edition cancels and replaces the first edition published in 2017. This edition constitutes a technical revision.

This edition includes the following significant technical changes with respect to the previous edition:

- a) a new subclause and annex relating to the problems associated with CDM testing of integrated circuits and discrete semiconductors in very small packages;
- b) changes to clarify cleaning of devices and testers.

The text of this International Standard is based on the following documents:

Draft	Report on voting
47/2746/FDIS	47/2754/RVD

Full information on the voting for its approval can be found in the report on voting indicated in the above table.

The language used for the development of this International Standard is English.

This document was drafted in accordance with ISO/IEC Directives, Part 2, and developed in accordance with ISO/IEC Directives, Part 1 and ISO/IEC Directives, IEC Supplement, available at www.iec.ch/members_experts/refdocs. The main document types developed by IEC are described in greater detail at www.iec.ch/standardsdev/publications.

A list of all parts in the IEC 60749 series, published under the general title *Semiconductor devices – Mechanical and climatic test methods*, can be found on the IEC website.

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INTRODUCTION

The earliest electrostatic discharge (ESD) test models and standards simulate a charged object approaching a device and discharging through the device. The most common example is IEC 60749-26, the human body model (HBM). However, with the increasing use of automated device handling systems, another potentially destructive discharge mechanism, the charged device model (CDM), becomes increasingly important. In the CDM, a device itself becomes charged (e.g. by sliding on a surface (tribocharging) or by electric field induction) and is rapidly discharged (by an ESD event) as it closely approaches a conductive object. A critical feature of the CDM is the metal-metal discharge, which results in a very rapid transfer of charge through an air breakdown arc. The CDM test method also simulates metal-metal discharges arising from other similar scenarios, such as the discharging of charged metal objects to devices at different potential.

Accurately quantifying and reproducing this fast metal-metal discharge event is very difficult, if not impossible, due to the limitations of the measuring equipment and its influence on the discharge event. The CDM discharge is generally completed in a few nanoseconds, and peak currents of tens of amperes have been observed. The peak current into the device will vary considerably depending on a large number of factors, including package type and parasitics. The typical failure mechanism observed in MOS devices for the CDM model is dielectric damage, although other damage has been noted.

The CDM charge voltage sensitivity of a given device is package dependent. For example, the same integrated circuit (IC) in a small area package can be less susceptible to CDM damage at a given voltage compared to that same IC in a package of the same type with a larger area. It has been shown that CDM damage susceptibility correlates better to peak current levels than charge voltage.

SEMICONDUCTOR DEVICES – MECHANICAL AND CLIMATIC TEST METHODS –

Part 28: Electrostatic discharge (ESD) sensitivity testing – Charged device model (CDM) – device level

1 Scope

This part of IEC 60749 establishes the procedure for testing, evaluating, and classifying devices and microcircuits according to their susceptibility (sensitivity) to damage or degradation by exposure to a defined field-induced charged device model (CDM) electrostatic discharge (ESD). All packaged semiconductor devices, thin film circuits, surface acoustic wave (SAW) devices, opto-electronic devices, hybrid integrated circuits (HICs), and multi-chip modules (MCMs) containing any of these devices are to be evaluated according to this document. To perform the tests, the devices are assembled into a package similar to that expected in the final application. This CDM document does not apply to socketed discharge model testers. This document describes the field-induced (FI) method. An alternative, the direct contact (DC) method, is described in Annex J.

The purpose of this document is to establish a test method that will replicate CDM failures and provide reliable, repeatable CDM ESD test results from tester to tester, regardless of device type. Repeatable data will allow accurate classifications and comparisons of CDM ESD sensitivity levels.

2 Normative references

There are no normative references in this document.

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